



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Kazuo MAEDA

Serial No.: 09/519,599

Filed: March 6, 2000

For: METHOD AND APPARATUS FOR
FORMING AN INTERLAYER
INSULATING FILM AND
SEMICONDUCTOR DEVICE

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) Examiner: Quach
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) Art Unit: 2814
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) ATTENTION ART UNIT 2814
) EXPEDITED PROCESSING
) RESPONSE TO FINAL ACTION

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J. Carter

RESPONSE TO FINAL REJECTION UNDER 37 CFR 1.116

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Responsive to the "final" action of August 27, 2002, please amend the captioned application

as follows:

IN THE CLAIMS:

Please cancel claims 2, 9, 10 and 12 and rewrite claims 1 and 11 as follows:

1. (Twice Amended) A method for forming an interlayer insulating film comprising the steps of:

(1) forming a SiO₂ film containing boron, carbon and H₂O on a substrate by plasma enhanced chemical vapor deposition using a source gas containing an Si-C-O-H compound, an oxidative gas and a compound containing boron; and

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